Lattice Semiconductor Corporation

MachXO Family Data Sheet Introduction

Data Sheet DS1002

Features

- **Non-volatile, Infinitely Reconfigurable**
  - Instant-on – powers up in microseconds
  - Single chip, no external configuration memory required
  - Excellent design security, no bit stream to intercept
  - Reconfigure SRAM based logic in milliseconds
  - SRAM and non-volatile memory programmable through JTAG port
  - Supports background programming of non-volatile memory
- **Sleep Mode**
  - Allows up to 100x static current reduction
- **TransFR™ Reconfiguration (TFR)**
  - In-field logic update while system operates
- **High I/O to Logic Density**
  - 256 to 2280 LUT4s
  - 73 to 271 I/Os with extensive package options
  - Density migration supported
  - Lead free/RoHS compliant packaging
- **Embedded and Distributed Memory**
  - Up to 27.6 Kbits sysMEM™ Embedded Block RAM
  - Up to 7.5 Kbits distributed RAM
  - Dedicated FIFO control logic
- **Flexible I/O Buffer**
  - Programmable sysIO™ buffer supports wide range of interfaces:
    - LVCMOS 3.3/2.5/1.8/1.5/1.2
    - LVTTL
    - PCI
    - LVDS, Bus-LVDS, LVPECL, RSDS
- **sysCLOCK™ PLLs**
  - Up to two analog PLLs per device
  - Clock multiply, divide, and phase shifting
- **System Level Support**
  - IEEE Standard 1149.1 Boundary Scan
  - Onboard oscillator
  - Devices operate with 3.3V, 2.5V, 1.8V or 1.2V power supply
  - IEEE 1532 compliant in-system programming

Introduction

The MachXO is optimized to meet the requirements of applications traditionally addressed by CPLDs and low capacity FPGAs: glue logic, bus bridging, bus interfacing, power-up control, and control logic. These devices bring together the best features of CPLD and FPGA devices on a single chip.

Table 1-1. MachXO Family Selection Guide

Device	LCMXO256	LCMXO640	LCMXO1200	LCMXO2280
LUTs	256	640	1200	2280
Dist. RAM (Kbits)	2.0	6.0	6.25	7.5
EBR SRAM (Kbits)	0	0	9.2	27.6
Number of EBR SRAM Blocks (9 Kbits)	0	0	1	3
V_{CC} Voltage	1.2/1.8/2.5/3.3V	1.2/1.8/2.5/3.3V	1.2/1.8/2.5/3.3V	1.2/1.8/2.5/3.3V
Number of PLLs	0	0	1	2
Max. I/O	78	159	211	271
Packages				
100-pin TQFP (14x14 mm)	78	74	73	73
144-pin TQFP (20x20 mm)		113	113	113
100-ball csBGA (8x8 mm)	78	74		
132-ball csBGA (8x8 mm)		101	101	101
256-ball ftBGA (17x17 mm)		159	211	211
324-ball ftBGA (19x19 mm)				271

The devices use look-up tables (LUTs) and embedded block memories traditionally associated with FPGAs for flexible and efficient logic implementation. Through non-volatile technology, the devices provide the single-chip, high-security, instant-on capabilities traditionally associated with CPLDs. Finally, advanced process technology and careful design will provide the high pin-to-pin performance also associated with CPLDs.

The ispLEVER® design tools from Lattice allow complex designs to be efficiently implemented using the MachXO family of devices. Popular logic synthesis tools provide synthesis library support for MachXO. The ispLEVER tools use the synthesis tool output along with the constraints from its floor planning tools to place and route the design in the MachXO device. The ispLEVER tool extracts the timing from the routing and back-annotates it into the design for timing verification.

Table 2-8. I/O Support Device by Device

	MachXO256	MachXO640	MachXO1200	MachXO2280
Number of I/O Banks	2	4	8	8
Type of Input Buffers	Single-ended (all I/O Banks)	Single-ended (all I/O Banks)	Single-ended (all I/O Banks) Differential Receivers (all I/O Banks)	Single-ended (all I/O Banks) Differential Receivers (all I/O Banks)
Types of Output Buffers	Single-ended buffers with complementary outputs (all I/O Banks)	Single-ended buffers with complementary outputs (all I/O Banks)	Single-ended buffers with complementary outputs (all I/O Banks) Differential buffers with true LVDS outputs (50% on left and right side)	Single-ended buffers with complementary outputs (all I/O Banks) Differential buffers with true LVDS outputs (50% on left and right side)
Differential Output Emulation Capability	All I/O Banks	All I/O Banks	All I/O Banks	All I/O Banks
PCI Support	No	No	Top side only	Top side only

Table 2-9. Supported Input Standards

	VCCIO (Typ.)				
Input Standard	**3.3V**	**2.5V**	**1.8V**	**1.5V**	**1.2V**
Single Ended Interfaces					
LVTTL	√	√	√	√	√
LVCMOS33	√	√	√	√	√
LVCMOS25	√	√	√	√	√
LVCMOS18			√		
LVCMOS15				√	
LVCMOS12	√	√	√	√	√
PCI[1]	√				
Differential Interfaces					
BLVDS[2], LVDS[2], LVPECL[2], RSDS[2]	√	√	√	√	√

1. Top Banks of MachXO1200 and MachXO2280 devices only.
2. MachXO1200 and MachXO2280 devices only.

MachXO Family Data Sheet
DC and Switching Characteristics

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Absolute Maximum Ratings[1, 2, 3]

	LCMXO E (1.2V)	LCMXO C (1.8V/2.5V/3.3V)
Supply Voltage V_{CC}	-0.5 to 1.32V	-0.5 to 3.75V
Supply Voltage V_{CCAUX}	-0.5 to 3.75V	-0.5 to 3.75V
Output Supply Voltage V_{CCIO}	-0.5 to 3.75V	-0.5 to 3.75V
I/O Tristate Voltage Applied [4]	-0.5 to 3.75V	-0.5 to 3.75V
Dedicated Input Voltage Applied[4]	-0.5 to 3.75V	-0.5 to 4.25V
Storage Temperature (ambient)	-65 to 150°C	-65 to 150°C
Junction Temp. (Tj)	+125°C	+125°C

1. Stress above those listed under the “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice *Thermal Management* document is required.
3. All voltages referenced to GND.
4. Overshoot and undershoot of -2V to (V_{IHMAX} + 2) volts is permitted for a duration of <20ns.

Recommended Operating Conditions[1]

Symbol	Parameter	Min.	Max.	Units
V_{CC}	Core Supply Voltage for 1.2V Devices	1.14	1.26	V
	Core Supply Voltage for 1.8V/2.5V/3.3V Devices	1.71	3.465	V
V_{CCAUX}[3]	Auxiliary Supply Voltage	3.135	3.465	V
V_{CCIO}[2]	I/O Driver Supply Voltage	1.14	3.465	V
t_{JCOM}	Junction Temperature Commercial Operation	0	+85	°C
t_{JIND}	Junction Temperature Industrial Operation	-40	100	°C
$t_{JFLASHCOM}$	Junction Temperature, Flash Programming, Commercial	0	+85	°C
$t_{JFLASHIND}$	Junction Temperature, Flash Programming, Industrial	-40	100	°C

1. Like power supplies must be tied together. For example, if V_{CCIO} and V_{CC} are both 2.5V, they must also be the same supply. 3.3V V_{CCIO} and 1.2V V_{CCIO} should be tied to V_{CCAUX} or 1.2V V_{CC} respectively.
2. See recommended voltages by I/O standard in subsequent table.
3. V_{CC} must reach minimum V_{CC} value before V_{CCAUX} reaches 2.5V.

MachXO256 and MachXO640 Hot Socketing Specifications[1, 2, 3]

Symbol	Parameter	Condition	Min.	Typ.	Max	Units
I_{DK}	Input or I/O leakage Current	$0 \le V_{IN} \le V_{IH}$ (MAX)	—	—	+/-1000	μA

1. Insensitive to sequence of V_{CC}, V_{CCAUX}, and V_{CCIO}. However, assumes monotonic rise/fall rates for V_{CC}, V_{CCAUX}, and V_{CCIO}.
2. $0 \le V_{CC} \le V_{CC}$ (MAX), $0 \le V_{CCIO} \le V_{CCIO}$ (MAX) and $0 \le V_{CCAUX} \le V_{CCAUX}$ (MAX).
3. I_{DK} is additive to I_{PU}, I_{PD} or I_{BH}.

MachXO1200 and MachXO2280 Hot Socketing Specifications[1, 2, 3, 4]

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
Non-LVDS General Purpose sysIOs						
I_{DK}	Input or I/O Leakage Current	$0 \leq V_{IN} \leq V_{IH}$ (MAX.)	—	—	+/-1000	µA
LVDS General Purpose sysIOs						
I_{DK_LVDS}	Input or I/O Leakage Current	$V_{IN} \leq V_{CCIO}$	—	—	+/-1000	µA
		$V_{IN} > V_{CCIO}$	—	35	—	mA

1. Insensitive to sequence of V_{CC}, V_{CCAUX}, and V_{CCIO}. However, assumes monotonic rise/fall rates for V_{CC}, V_{CCAUX}, and V_{CCIO}.
2. $0 \leq V_{CC} \leq V_{CC}$ (MAX), $0 \leq V_{CCIO} \leq V_{CCIO}$ (MAX), and $0 \leq V_{CCAUX} \leq V_{CCAUX}$ (MAX).
3. I_{DK} is additive to I_{PU}, I_{PW} or I_{BH}.
4. LVCMOS and LVTTL only.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
I_{IL}, I_{IH}[1, 4, 5]	Input or I/O Leakage	$0 \leq V_{IN} \leq (V_{CCIO} - 0.2V)$	—	—	10	µA
		$(V_{CCIO} - 0.2V) < V_{IN} \leq 3.6V$	—	—	40	µA
I_{PU}	I/O Active Pull-up Current	$0 \leq V_{IN} \leq 0.7 V_{CCIO}$	-30	—	-150	µA
I_{PD}	I/O Active Pull-down Current	V_{IL} (MAX) $\leq V_{IN} \leq V_{IH}$ (MAX)	30	—	150	µA
I_{BHLS}	Bus Hold Low sustaining current	$V_{IN} = V_{IL}$ (MAX)	30	—	—	µA
I_{BHHS}	Bus Hold High sustaining current	$V_{IN} = 0.7V_{CCIO}$	-30	—	—	µA
I_{BHLO}	Bus Hold Low Overdrive current	$0 \leq V_{IN} \leq V_{IH}$ (MAX)	—	—	150	µA
I_{BHHO}	Bus Hold High Overdrive current	$0 \leq V_{IN} \leq V_{IH}$ (MAX)	—	—	-150	µA
V_{BHT}[3]	Bus Hold trip Points	$0 \leq V_{IN} \leq V_{IH}$ (MAX)	V_{IL} (MAX)	—	V_{IH} (MIN)	V
C1	I/O Capacitance[2]	V_{CCIO} = 3.3V, 2.5V, 1.8V, 1.5V, 1.2V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	—	8	—	pf
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3V, 2.5V, 1.8V, 1.5V, 1.2V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	—	8	—	pf

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25°C, f = 1.0MHz
3. Please refer to V_{IL} and V_{IH} in the sysIO Single-Ended DC Electrical Characteristics table of this document.
4. Not applicable to SLEEPN pin.
5. When V_{IH} is higher than V_{CCIO}, a transient current typically of 30ns in duration or less with a peak current of 6mA can occur on the high-to-low transition. For MachXO1200 and MachXO2280 true LVDS output pins, V_{IH} must be less than or equal to V_{CCIO}.

Supply Current (Sleep Mode)[1, 2]

Symbol	Parameter	Device	Typ.[3]	Max.	Units
I_{CC}	Core Power Supply	LCMXO256C	12	25	µA
		LCMXO640C	12	25	µA
		LCMXO1200C	12	25	µA
		LCMXO2280C	12	25	µA
I_{CCAUX}	Auxiliary Power Supply	LCMXO256C	1	15	µA
		LCMXO640C	1	25	µA
		LCMXO1200C	1	45	µA
		LCMXO2280C	1	85	µA
I_{CCIO}	Bank Power Supply[4]	All LCMXO 'C' Devices	2	30	µA

1. Assumes all inputs are configured as LVCMOS and held at the VCCIO or GND.
2. Frequency = 0MHz.
3. T_A = 25°C, power supplies at nominal voltage.
4. Per Bank.

Supply Current (Standby)[1, 2, 3, 4]

Over Recommended Operating Conditions

Symbol	Parameter	Device	Typ.[5]	Units
I_{CC}	Core Power Supply	LCMXO256C	7	mA
		LCMXO640C	9	mA
		LCMXO1200C	14	mA
		LCMXO2280C	20	mA
		LCMXO256E	4	mA
		LCMXO640E	6	mA
		LCMXO1200E	10	mA
		LCMXO2280E	12	mA
I_{CCAUX}	Auxiliary Power Supply V_{CCAUX} = 3.3V	LCMXO256E/C	5	mA
		LCMXO640E/C	7	mA
		LCMXO1200E/C	12	mA
		LCMXO2280E/C	13	mA
I_{CCIO}	Bank Power Supply[6]	All devices	2	mA

1. For further information on supply current, please see details of additional technical documentation at the end of this data sheet.
2. Assumes all outputs are tristated, all inputs are configured as LVCMOS and held at V_{CCIO} or GND.
3. Frequency = 0MHz.
4. User pattern = blank.
5. T_J = 25°C, power supplies at nominal voltage.
6. Per Bank. V_{CCIO} = 2.5V. Does not include pull-up/pull-down.

Initialization Supply Current[1, 2, 3, 4]

Over Recommended Operating Conditions

Symbol	Parameter	Device	Typ.[5]	Units
I_{CC}	Core Power Supply	LCMXO256C	13	mA
		LCMXO640C	17	mA
		LCMXO1200C	21	mA
		LCMXO2280C	23	mA
		LCMXO256E	10	mA
		LCMXO640E	14	mA
		LCMXO1200E	18	mA
		LCMXO2280E	20	mA
I_{CCAUX}	Auxiliary Power Supply V_{CCAUX} = 3.3V	LCMXO256E/C	10	mA
		LCMXO640E/C	13	mA
		LCMXO1200E/C	24	mA
		LCMXO2280E/C	25	mA
I_{CCIO}	Bank Power Supply[6]	All devices	2	mA

1. For further information on supply current, please see details of additional technical documentation at the end of this data sheet.
2. Assumes all I/O pins are held at V_{CCIO} or GND.
3. Frequency = 0MHz.
4. Typical user pattern.
5. T_J = 25°C, power supplies at nominal voltage.
6. Per Bank, V_{CCIO} = 2.5V. Does not include pull-up/pull-down.

Programming and Erase Flash Supply Current[1, 2, 3, 4]

Symbol	Parameter	Device	Typ.[5]	Units
I_{CC}	Core Power Supply	LCMXO256C	9	mA
		LCMXO640C	11	mA
		LCMXO1200C	16	mA
		LCMXO2280C	22	mA
		LCMXO256E	6	mA
		LCMXO640E	8	mA
		LCMXO1200E	12	mA
		LCMXO2280E	14	mA
I_{CCAUX}	Auxiliary Power Supply V_{CCAUX} = 3.3V	LCMXO256C/E	8	mA
		LCMXO640C/E	10	mA
		LCMXO1200/E	15	mA
		LCMXO2280C/E	16	mA
I_{CCIO}	Bank Power Supply[6]	All devices	2	mA

1. For further information on supply current, please see details of additional technical documentation at the end of this data sheet.
2. Assumes all I/O pins are held at V_{CCIO} or GND.
3. Typical user pattern.
4. JTAG programming is at 25MHz.
5. T_J = 25°C, power supplies at nominal voltage.
6. Per Bank. V_{CCIO} = 2.5V. Does not include pull-up/pull-down.

MachXO Internal Timing Parameters[1]

Over Recommended Operating Conditions

Parameter	Description	-5		-4		-3		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
PFU/PFF Logic Mode Timing								
t_{LUT4_PFU}	LUT4 delay (A to D inputs to F output)	—	0.28	—	0.34	—	0.39	ns
t_{LUT6_PFU}	LUT6 delay (A to D inputs to OFX output)	—	0.44	—	0.53	—	0.62	ns
t_{LSR_PFU}	Set/Reset to output of PFU	—	0.90	—	1.08	—	1.26	ns
t_{SUM_PFU}	Clock to Mux (M0,M1) input setup time	0.10	—	0.13	—	0.15	—	ns
t_{HM_PFU}	Clock to Mux (M0,M1) input hold time	-0.05	—	-0.06	—	-0.07	—	ns
t_{SUD_PFU}	Clock to D input setup time	0.13	—	0.16	—	0.18	—	ns
t_{HD_PFU}	Clock to D input hold time	-0.03	—	-0.03	—	-0.04	—	ns
t_{CK2Q_PFU}	Clock to Q delay, D-type register configuration	—	0.40	—	0.48	—	0.56	ns
t_{LE2Q_PFU}	Clock to Q delay latch configuration	—	0.53	—	0.64	—	0.74	ns
t_{LD2Q_PFU}	D to Q throughput delay when latch is enabled	—	0.55	—	0.66	—	0.77	ns
PFU Dual Port Memory Mode Timing								
t_{CORAM_PFU}	Clock to Output	—	0.40	—	0.48	—	0.56	ns
t_{SUDATA_PFU}	Data Setup Time	-0.18	—	-0.22	—	-0.25	—	ns
t_{HDATA_PFU}	Data Hold Time	0.28	—	0.34	—	0.39	—	ns
t_{SUADDR_PFU}	Address Setup Time	-0.46	—	-0.56	—	-0.65	—	ns
t_{HADDR_PFU}	Address Hold Time	0.71	—	0.85	—	0.99	—	ns
t_{SUWREN_PFU}	Write/Read Enable Setup Time	-0.22	—	-0.26	—	-0.30	—	ns
t_{HWREN_PFU}	Write/Read Enable Hold Time	0.33	—	0.40	—	0.47	—	ns
PIO Input/Output Buffer Timing								
t_{IN_PIO}	Input Buffer Delay	—	0.75	—	0.90	—	1.06	ns
t_{OUT_PIO}	Output Buffer Delay	—	1.29	—	1.54	—	1.80	ns
EBR Timing (1200 and 2280 Devices Only)								
t_{CO_EBR}	Clock to output from Address or Data with no output register	—	2.24	—	2.69	—	3.14	ns
t_{COO_EBR}	Clock to output from EBR output Register	—	0.54	—	0.64	—	0.75	ns
t_{SUDATA_EBR}	Setup Data to EBR Memory	-0.26	—	-0.31	—	-0.37	—	ns
t_{HDATA_EBR}	Hold Data to EBR Memory	0.41	—	0.49	—	0.57	—	ns
t_{SUADDR_EBR}	Setup Address to EBR Memory	-0.26	—	-0.31	—	-0.37	—	ns
t_{HADDR_EBR}	Hold Address to EBR Memory	0.41	—	0.49	—	0.57	—	ns
t_{SUWREN_EBR}	Setup Write/Read Enable to EBR Memory	-0.17	—	-0.20	—	-0.23	—	ns
t_{HWREN_EBR}	Hold Write/Read Enable to EBR Memory	0.26	—	0.31	—	0.36	—	ns
t_{SUCE_EBR}	Clock Enable Setup Time to EBR Output Register	0.19	—	0.23	—	0.27	—	ns
t_{HCE_EBR}	Clock Enable Hold Time to EBR Output Register	-0.13	—	-0.16	—	-0.18	—	ns
t_{RSTO_EBR}	Reset To Output Delay Time from EBR Output Register	—	1.03	—	1.23	—	1.44	ns
PLL Parameters (1200 and 2280 Devices Only)								
t_{RSTREC}	Reset Recovery to Rising Clock	1.00	—	1.00	—	1.00	—	ns
t_{RSTSU}	Reset Signal Setup Time	1.00	—	1.00	—	1.00	—	ns

1. Internal parameters are characterized but not tested on every device.

Lattice Semiconductor Corporation

MachXO Family Data Sheet
Ordering Information

Data Sheet DS1002

Part Number Description

LCMXO XXXX X – X XXXXXX X XX

Device Family
MachXO PLD

Logic Capacity
256 LUTs = 256
640 LUTs = 640
1200 LUTs = 1200
2280 LUTs = 2280

Supply Voltage
C = 1.8V/2.5V/3.3V
E = 1.2V

Note: Parts dual marked as described.

ES = Engineering Sample
Blank = Production Device

Grade
C = Commercial
I = Industrial

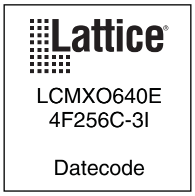
Package
T100 = 100-pin TQFP
T144 = 144-pin TQFP
M100 = 100-ball csBGA
M132 = 132-ball csBGA
FT256 = 256-ball ftBGA
FT324 = 324-ball ftBGA

TN100 = 100-pin Lead-Free TQFP
TN144 = 144-pin Lead-Free TQFP
MN100 = 100-ball Lead-Free csBGA
MN132 = 132-ball Lead-Free csBGA
FTN256 = 256-ball Lead-Free ftBGA
FTN324 = 324-ball Lead-Free ftBGA

Speed
3 = Slowest
4
5 = Fastest

Ordering Information

Note: MachXO devices are dual marked except the slowest commercial speed grade device. For example the commercial speed grade LCMXO640E-4F256C is also marked with industrial grade -3I grade. The slowest commercial speed grade does not have industrial markings. The markings appears as follows:



Dual Mark

Part Number	LUTs	Supply Voltage	I/Os	Grade	Package	Pins	Temp.
LCMXO2280C-3TN144C	2280	1.8V/2.5V/3.3V	113	-3	Lead-Free TQFP	144	COM
LCMXO2280C-4TN144C	2280	1.8V/2.5V/3.3V	113	-4	Lead-Free TQFP	144	COM
LCMXO2280C-5TN144C	2280	1.8V/2.5V/3.3V	113	-5	Lead-Free TQFP	144	COM
LCMXO2280C-3MN132C	2280	1.8V/2.5V/3.3V	101	-3	Lead-Free csBGA	132	COM
LCMXO2280C-4MN132C	2280	1.8V/2.5V/3.3V	101	-4	Lead-Free csBGA	132	COM
LCMXO2280C-5MN132C	2280	1.8V/2.5V/3.3V	101	-5	Lead-Free csBGA	132	COM
LCMXO2280C-3FTN256C	2280	1.8V/2.5V/3.3V	211	-3	Lead-Free ftBGA	256	COM
LCMXO2280C-4FTN256C	2280	1.8V/2.5V/3.3V	211	-4	Lead-Free ftBGA	256	COM
LCMXO2280C-5FTN256C	2280	1.8V/2.5V/3.3V	211	-5	Lead-Free ftBGA	256	COM
LCMXO2280C-3FTN324C	2280	1.8V/2.5V/3.3V	271	-3	Lead-Free ftBGA	324	COM
LCMXO2280C-4FTN324C	2280	1.8V/2.5V/3.3V	271	-4	Lead-Free ftBGA	324	COM
LCMXO2280C-5FTN324C	2280	1.8V/2.5V/3.3V	271	-5	Lead-Free ftBGA	324	COM

Part Number	LUTs	Supply Voltage	I/Os	Grade	Package	Pins	Temp.
LCMXO256E-3TN100C	256	1.2V	78	-3	Lead-Free TQFP	100	COM
LCMXO256E-4TN100C	256	1.2V	78	-4	Lead-Free TQFP	100	COM
LCMXO256E-5TN100C	256	1.2V	78	-5	Lead-Free TQFP	100	COM
LCMXO256E-3MN100C	256	1.2V	78	-3	Lead-Free csBGA	100	COM
LCMXO256E-4MN100C	256	1.2V	78	-4	Lead-Free csBGA	100	COM
LCMXO256E-5MN100C	256	1.2V	78	-5	Lead-Free csBGA	100	COM

Part Number	LUTs	Supply Voltage	I/Os	Grade	Package	Pins	Temp.
LCMXO640E-3TN100C	640	1.2V	74	-3	Lead-Free TQFP	100	COM
LCMXO640E-4TN100C	640	1.2V	74	-4	Lead-Free TQFP	100	COM
LCMXO640E-5TN100C	640	1.2V	74	-5	Lead-Free TQFP	100	COM
LCMXO640E-3MN100C	640	1.2V	74	-3	Lead-Free csBGA	100	COM
LCMXO640E-4MN100C	640	1.2V	74	-4	Lead-Free csBGA	100	COM
LCMXO640E-5MN100C	640	1.2V	74	-5	Lead-Free csBGA	100	COM
LCMXO640E-3TN144C	640	1.2V	113	-3	Lead-Free TQFP	144	COM
LCMXO640E-4TN144C	640	1.2V	113	-4	Lead-Free TQFP	144	COM
LCMXO640E-5TN144C	640	1.2V	113	-5	Lead-Free TQFP	144	COM
LCMXO640E-3MN132C	640	1.2V	101	-3	Lead-Free csBGA	132	COM
LCMXO640E-4MN132C	640	1.2V	101	-4	Lead-Free csBGA	132	COM
LCMXO640E-5MN132C	640	1.2V	101	-5	Lead-Free csBGA	132	COM
LCMXO640E-3FTN256C	640	1.2V	159	-3	Lead-Free ftBGA	256	COM
LCMXO640E-4FTN256C	640	1.2V	159	-4	Lead-Free ftBGA	256	COM
LCMXO640E-5FTN256C	640	1.2V	159	-5	Lead-Free ftBGA	256	COM

Lead-Free Packaging

Industrial

Part Number	LUTs	Supply Voltage	I/Os	Grade	Package	Pins	Temp.
LCMXO256C-3TN100I	256	1.8V/2.5V/3.3V	78	-3	Lead-Free TQFP	100	IND
LCMXO256C-4TN100I	256	1.8V/2.5V/3.3V	78	-4	Lead-Free TQFP	100	IND
LCMXO256C-3MN100I	256	1.8V/2.5V/3.3V	78	-3	Lead-Free csBGA	100	IND
LCMXO256C-4MN100I	256	1.8V/2.5V/3.3V	78	-4	Lead-Free csBGA	100	IND

Part Number	LUTs	Supply Voltage	I/Os	Grade	Package	Pins	Temp.
LCMXO640C-3TN100I	640	1.8V/2.5V/3.3V	74	-3	Lead-Free TQFP	100	IND
LCMXO640C-4TN100I	640	1.8V/2.5V/3.3V	74	-4	Lead-Free TQFP	100	IND
LCMXO640C-3MN100I	640	1.8V/2.5V/3.3V	74	-3	Lead-Free csBGA	100	IND
LCMXO640C-4MN100I	640	1.8V/2.5V/3.3V	74	-4	Lead-Free csBGA	100	IND
LCMXO640C-3TN144I	640	1.8V/2.5V/3.3V	113	-3	Lead-Free TQFP	144	IND
LCMXO640C-4TN144I	640	1.8V/2.5V/3.3V	113	-4	Lead-Free TQFP	144	IND
LCMXO640C-3MN132I	640	1.8V/2.5V/3.3V	101	-3	Lead-Free csBGA	132	IND
LCMXO640C-4MN132I	640	1.8V/2.5V/3.3V	101	-4	Lead-Free csBGA	132	IND
LCMXO640C-3FTN256I	640	1.8V/2.5V/3.3V	159	-3	Lead-Free ftBGA	256	IND
LCMXO640C-4FTN256I	640	1.8V/2.5V/3.3V	159	-4	Lead-Free ftBGA	256	IND

Part Number	LUTs	Supply Voltage	I/Os	Grade	Package	Pins	Temp.
LCMXO1200C-3TN100I	1200	1.8V/2.5V/3.3V	73	-3	Lead-Free TQFP	100	IND
LCMXO1200C-4TN100I	1200	1.8V/2.5V/3.3V	73	-4	Lead-Free TQFP	100	IND
LCMXO1200C-3TN144I	1200	1.8V/2.5V/3.3V	113	-3	Lead-Free TQFP	144	IND
LCMXO1200C-4TN144I	1200	1.8V/2.5V/3.3V	113	-4	Lead-Free TQFP	144	IND
LCMXO1200C-3MN132I	1200	1.8V/2.5V/3.3V	101	-3	Lead-Free csBGA	132	IND
LCMXO1200C-4MN132I	1200	1.8V/2.5V/3.3V	101	-4	Lead-Free csBGA	132	IND
LCMXO1200C-3FTN256I	1200	1.8V/2.5V/3.3V	211	-3	Lead-Free ftBGA	256	IND
LCMXO1200C-4FTN256I	1200	1.8V/2.5V/3.3V	211	-4	Lead-Free ftBGA	256	IND

Part Number	LUTs	Supply Voltage	I/Os	Grade	Package	Pins	Temp.
LCMXO2280C-3TN100I	2280	1.8V/2.5V/3.3V	73	-3	Lead-Free TQFP	100	IND
LCMXO2280C-4TN100I	2280	1.8V/2.5V/3.3V	73	-4	Lead-Free TQFP	100	IND
LCMXO2280C-3TN144I	2280	1.8V/2.5V/3.3V	113	-3	Lead-Free TQFP	144	IND
LCMXO2280C-4TN144I	2280	1.8V/2.5V/3.3V	113	-4	Lead-Free TQFP	144	IND
LCMXO2280C-3MN132I	2280	1.8V/2.5V/3.3V	101	-3	Lead-Free csBGA	132	IND
LCMXO2280C-4MN132I	2280	1.8V/2.5V/3.3V	101	-4	Lead-Free csBGA	132	IND
LCMXO2280C-3FTN256I	2280	1.8V/2.5V/3.3V	211	-3	Lead-Free ftBGA	256	IND
LCMXO2280C-4FTN256I	2280	1.8V/2.5V/3.3V	211	-4	Lead-Free ftBGA	256	IND
LCMXO2280C-3FTN324I	2280	1.8V/2.5V/3.3V	271	-3	Lead-Free ftBGA	324	IND
LCMXO2280C-4FTN324I	2280	1.8V/2.5V/3.3V	271	-4	Lead-Free ftBGA	324	IND